

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P03R uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for use as a load switch or in PWM applications.

Application

- Load switch
- PWM application

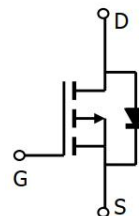
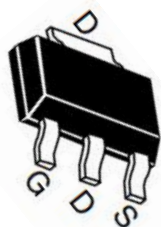
100% UIS TESTED!

100% ΔV_{ds} TESTED!

General Features

- $V_{DS} = -60V, I_D = -3A$
- $R_{DS(ON)} < 170m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 220m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- 150 °C operating temperature
- Pb-free lead plating

SOT-223-3L



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P03R	NCE60P03R	SOT-223-3L	Ø330mm	16mm	2500 units

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_A = 25^\circ C$)	I_D	-3	A
Drain Current-Continuous ($T_A = 70^\circ C$)	I_D	-2.4	A
Pulsed Drain Current (Note 1)	I_{DM}	-12	A
Maximum Power Dissipation	P_D	2.75	W
Single pulse avalanche energy (Note 5)	E_{AS}	24	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	45.5	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	35	$^\circ C/W$

Electrical Characteristics (T_A=25°C unless otherwise noted)

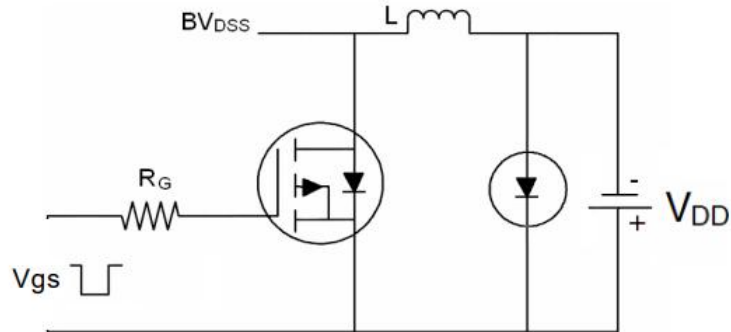
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.4	-2.0	-2.6	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-3A	-	148	170	mΩ
		V _{GS} =-4.5V, I _D =-3A	-	185	220	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-3A	-	3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	444.2	-	PF
Output Capacitance	C _{oss}		-	19.6	-	PF
Reverse Transfer Capacitance	C _{rss}		-	17.9	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, I _D =-3A, V _{GS} =-10V, R _G =3Ω	-	40	-	nS
Turn-on Rise Time	t _r		-	35	-	nS
Turn-Off Delay Time	t _{d(off)}		-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-3A, V _{GS} =-10V	-	11.3	-	nC
Gate-Source Charge	Q _{gs}		-	2.7	-	nC
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-3A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-3	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = - 3A	-	25		nS
Reverse Recovery Charge	Q _{rr}	di/dt = -100A/μs ^(Note3)	-	31		nC

Notes:

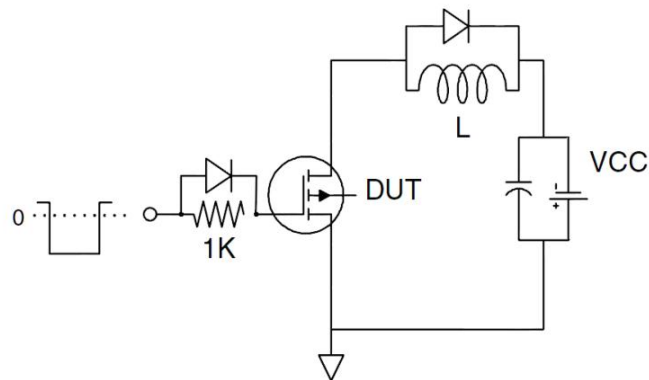
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=-30V, V_G=-10V, L=0.5mH, R_G=25Ω

Test Circuit

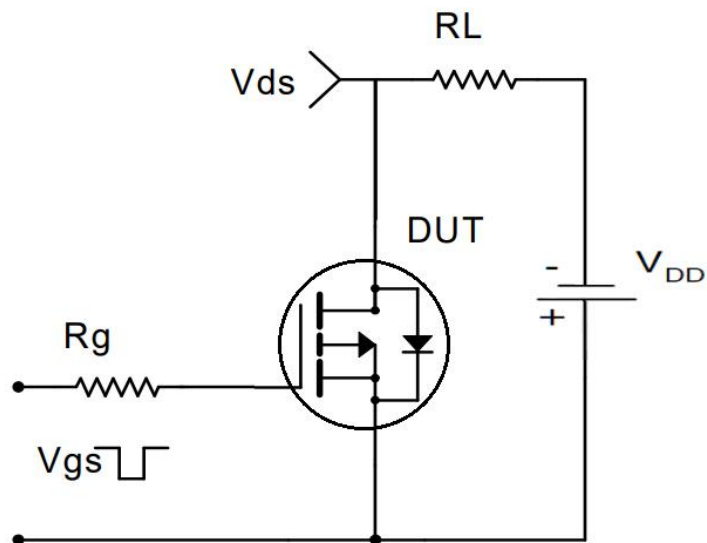
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

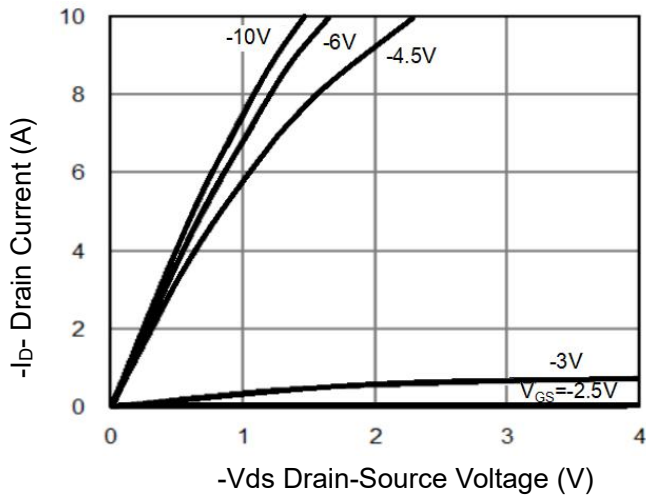


Figure 1 Output Characteristics

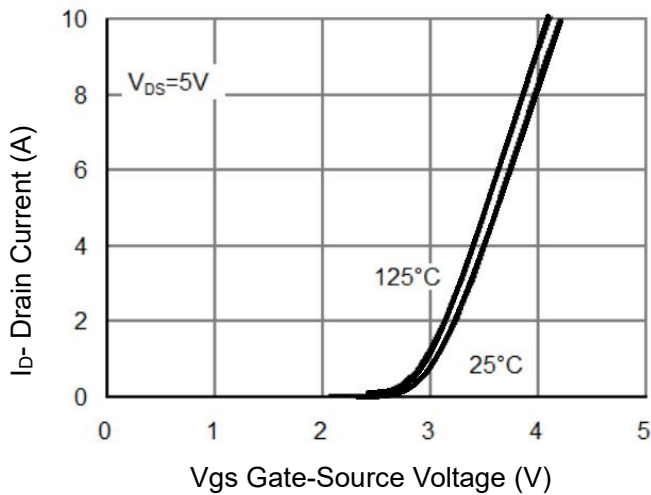


Figure 2 Transfer Characteristics

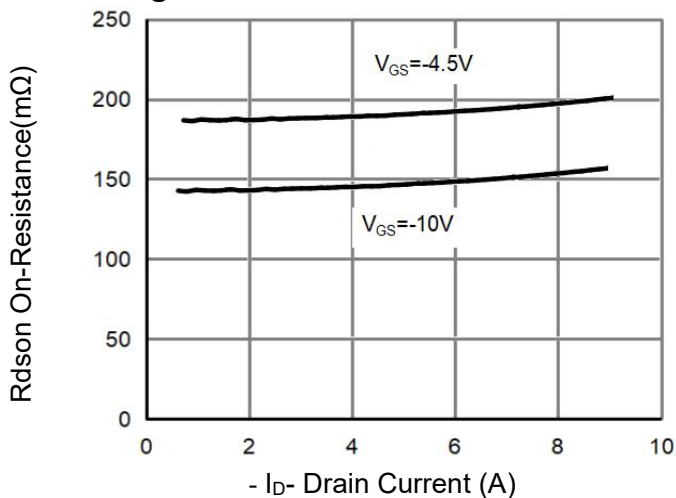


Figure 3 Rdson- Drain Current

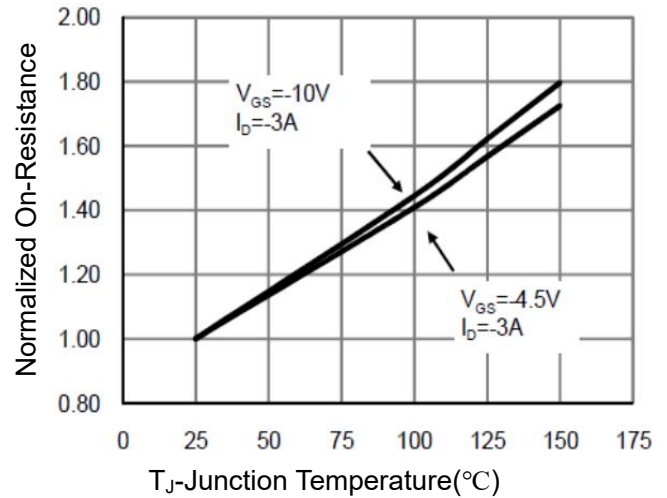


Figure 4 Rdson-Junction Temperature

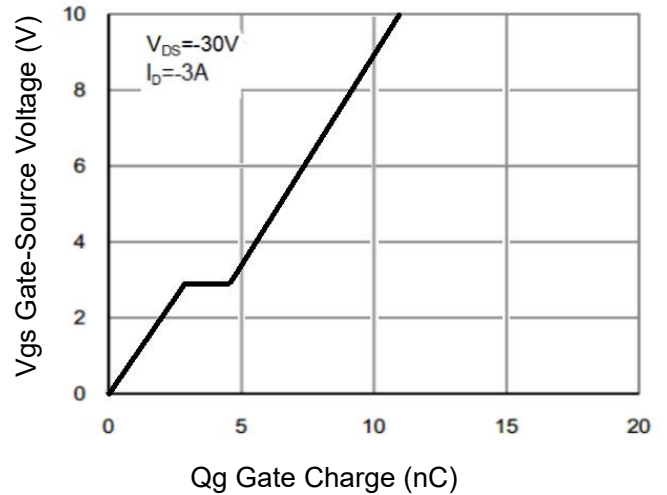


Figure 5 Gate Charge

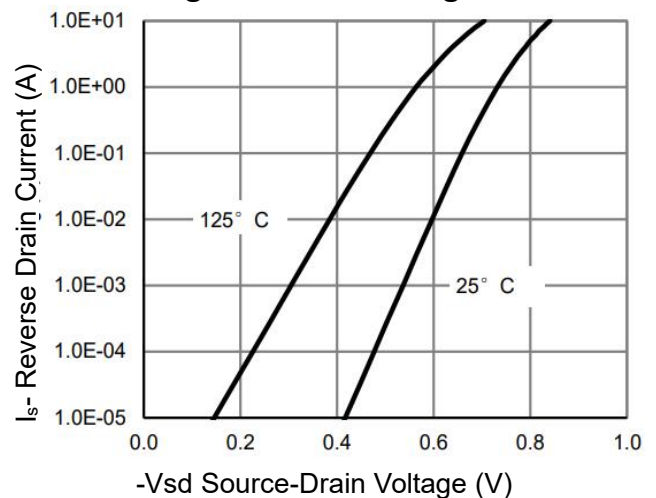


Figure 6 Source- Drain Diode Forward

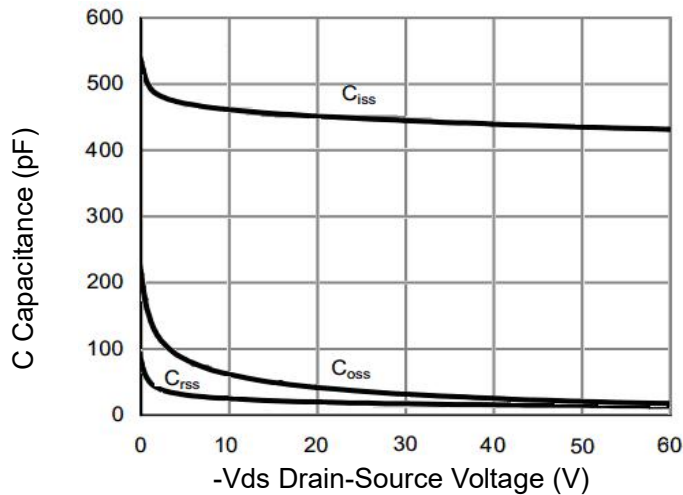


Figure 7 Capacitance vs Vds

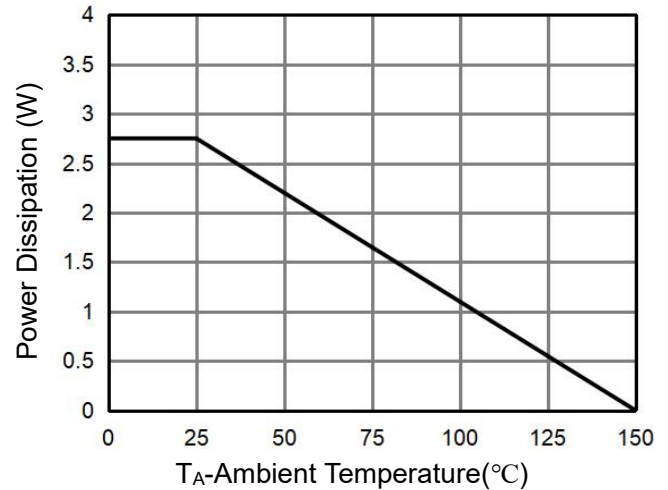


Figure 9 Power De-rating

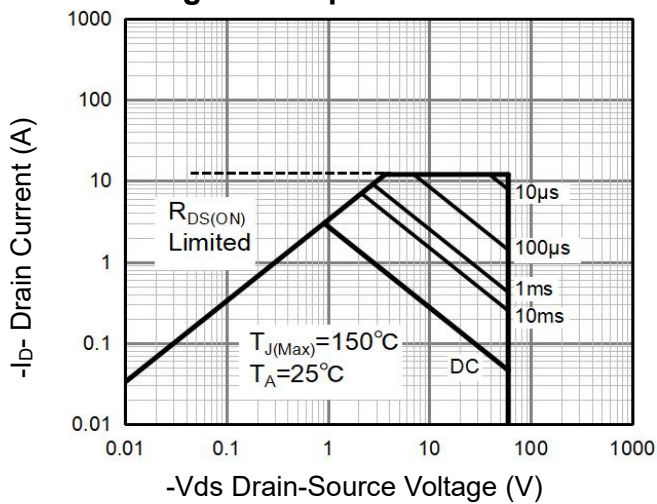


Figure 8 Safe Operation Area

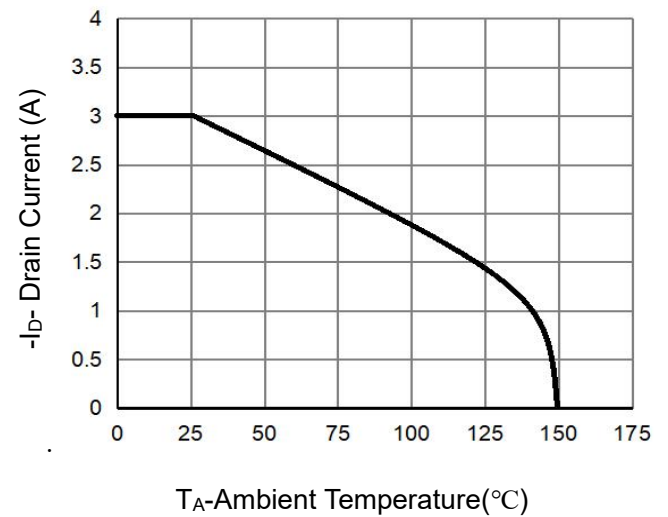


Figure 10 ID Current De-rating

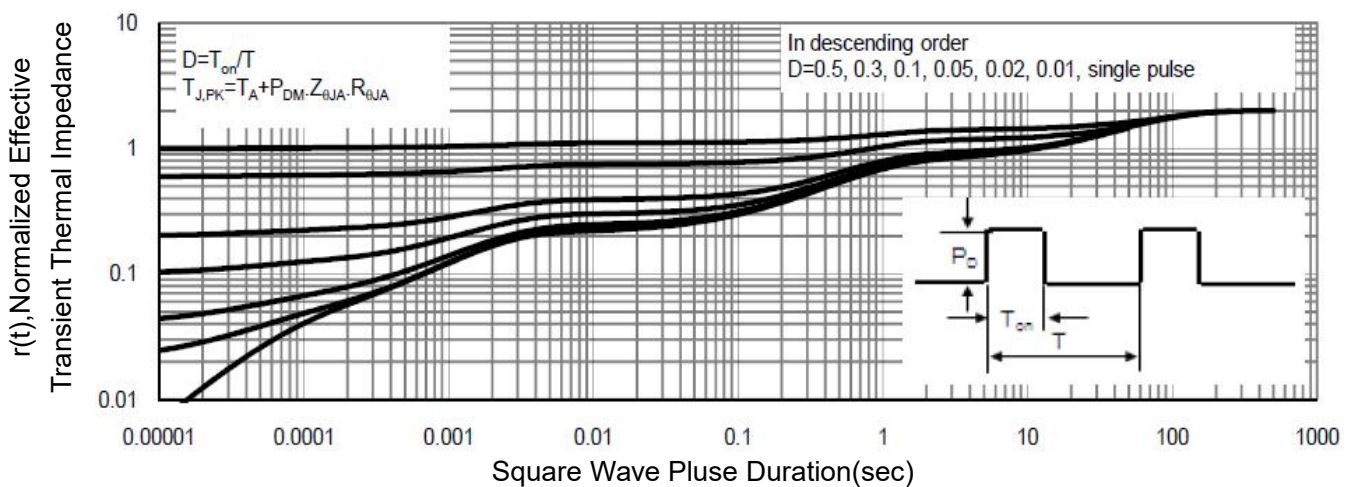
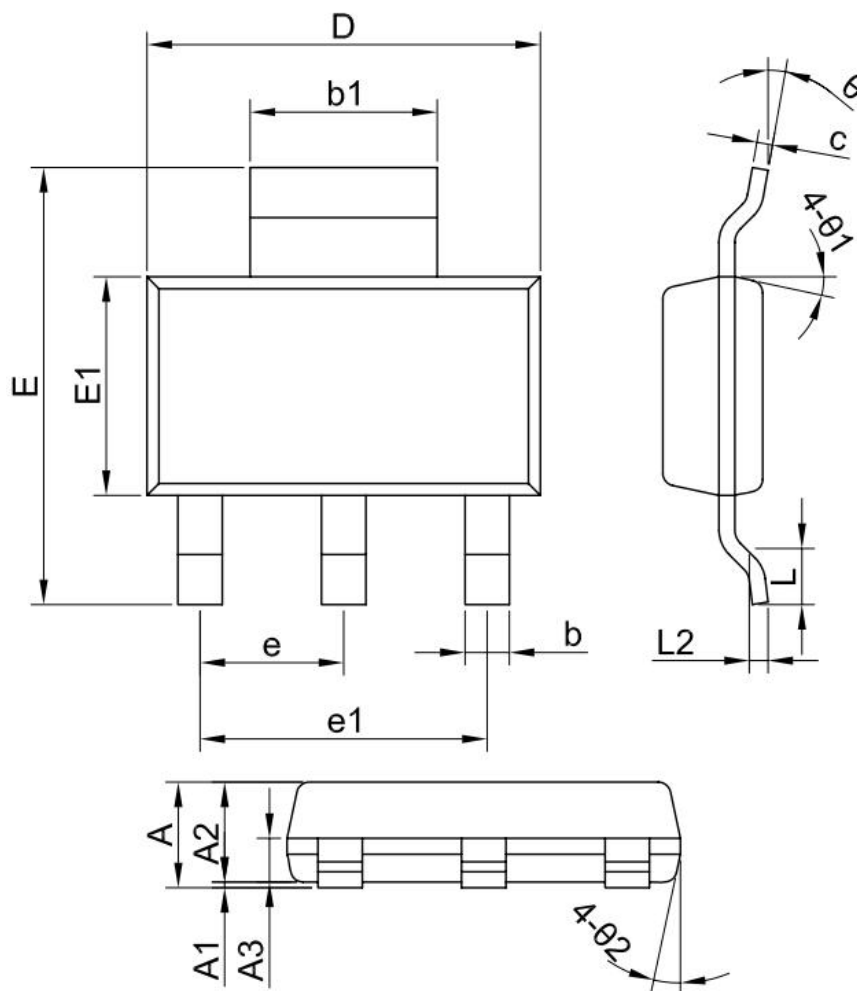


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-223-3L Package Information



SYMBOL	MIN	NOM	MAX
A	1.55	—	1.80
A1	0.02	—	0.12
A2	1.45	1.60	1.75
A3	0.60	0.70	0.80
b	0.60	—	0.80
b1	2.90	—	3.10
c	0.24	—	0.32
D	6.20	6.30	6.50
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.299REF		
e1	4.598REF		
L	0.90MIN		
L2	0.30BSC		
θ	0°	—	10°
θ_1	10°	12°	14°
θ_2	10°	12°	14°

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